

KSE5020

Feature

- High Voltage, High Quality High Speed Switching : t_F=0.1μs
- WIDE SOA



NPN Silicon Transistor

Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	800	V
V _{CEO}	Collector-Emitter Voltage	500	V
V _{EBO}	Emitter-Base Voltage	7	V
I _C	Collector Current (DC)	3	Α
I _{CP}	Collector Current (Pulse)	6	Α
I _B	Base Current (DC)	1	Α
P _C	Collector Dissipation (T _C =25°C)	30	W
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 55 ~ 150	°C

Electrical Characteristics $T_C=25^{\circ}C$ unless otherwise noted

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Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	$I_{C} = 1 \text{mA}, I_{E} = 0$	800			V
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_C = 5mA, R_{BE} = \infty$	500			V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_E = 1 \text{mA}, I_C = 0$	7			V
V _{CEX} (sus)	Collector-Emitter Sustaining Voltage	$I_C = 1.5A$, $I_B 1 = -I_B 2 = 0.6A$ L = 2mH, Clamped	500			V
I _{CBO}	Collector Cut-off Current	$V_{CB} = 500V, I_{E} = 0$			10	μΑ
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 5V, I_{C} = 0$			10	μΑ
h _{FE1}	DC Current Gain	$V_{CE} = 5V, I_{C} = 0.3A$	15		50	
h _{FE2}		$V_{CE} = 5V, I_{C} = 1.5A$	8			
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$I_C = 1.5A, I_B = 0.3A$			1	V
V _{BE} (sat)	Base-Emitter Saturation Voltage	$I_C = 1.5A, I_B = 0.3A$			1.5	V
C _{ob}	Output Capacitance	V _{CB} = 10V, f = 1MHz		50		pF
f _T	Current Gain Bandwidth Product	$V_{CE} = 10V, I_{C} = 0.3A$		18		MHz
t _{ON}	Turn ON Time	V _{CC} = 200V			0.5	μs
t _S	Storage Time	$5I_B1 = -2.5I_B2 = I_C = 2A$			3	μs
t _F	Fall Time	$RL = 100\Omega$			0.3	μs

h_{FE} Classification

Classification	R	0	Υ	
h _{FE1}	15 ~ 30	20 ~ 40	30 ~ 50	

Typical Characteristics

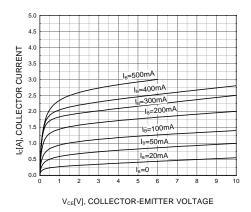


Figure 1. Static Characteristic

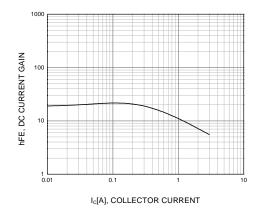


Figure 2. DC current Gain

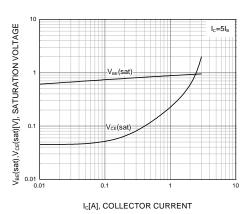


Figure 3. Collector-Emitter Saturation Voltage Baser-Emitter Saturation Voltage

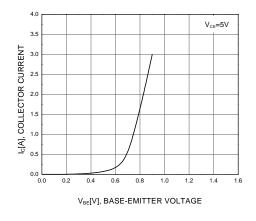


Figure 4. Base-Emitter On Voltage

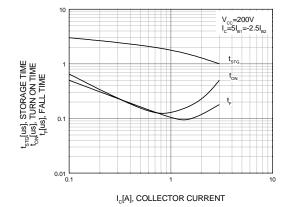


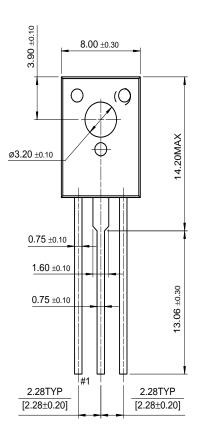
Figure 5. Turn On Time

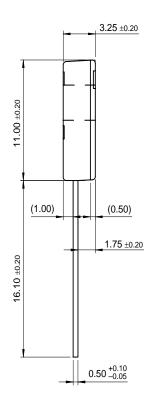
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KSE5020

Package Demensions

TO-126





Dimensions in Millimeters

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